

NPN RF POWER TRANSISTOR

DESCRIPTION:

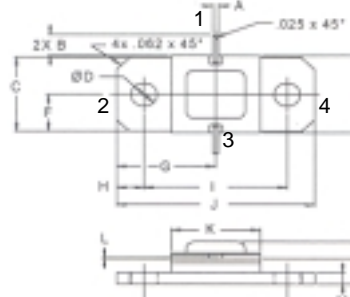
The **ASI MS2601** is Common Base Device Designed for Pulsed S-Band Radar Amplifier Applications up to 3.1 GHz.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	0.45 A
V_{CC}	34 V
P_{DISS}	11.5 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	13.0 °C/W

PACKAGE STYLE 400 x 400 2NL FLG


DIM	MINIMUM Inches / mm	MAXIMUM Inches / mm
A	.020 / 0.51	.030 / 0.76
B	.100 / 2.54	
C	.376 / 9.55	.396 / 10.06
D	.110 / 2.79	.130 / 3.30
E	.395 / 10.03	.407 / 10.34
F		.193 / 4.90
G		.450 / 11.43
H		.125 / 3.18
I	.640 / 16.26	.660 / 16.76
J	.890 / 22.61	.910 / 23.11
K	.395 / 10.03	.415 / 10.54
L	.084 / 0.10	.097 / 0.18
M	.052 / 1.32	.072 / 1.83
N	.116 / 3.00	.131 / 3.33
P		.230 / 5.84

1 = COLLECTOR 2 & 4 = BASE
3 = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 1.0\text{ mA}$	45			V
BV_{CER}	$I_C = 1.0\text{ mA}$	45			V
BV_{EBO}	$I_E = 1.0\text{ mA}$	3.5			V
I_{CES}	$V_{CE} = 30\text{ V}$			0.5	mA
h_{FE}	$V_{CE} = 5\text{ V}$ $I_C = 100\text{ mA}$	10		150	---
P_{OUT}	$V_{CC} = 30\text{ V}$ $P_{IN} = 0.3\text{ W}$ $f = 2700\text{ to }3100\text{ MHz}$	1.0			W
P_G	Pulse Width = 100 μS Duty Cycle = 10%	5.2			dB
η_c		27			%